

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		(438/149.ccls. or 257/72.ccls.)	USPAT	OR	OFF	2008/03/09 07:43
S1	115	thin same film\$6 same transistor\$1 same backplane	USPAT	OR	OFF	2008/03/06 13:29
S2	153	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 13:31
S3	5	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and first same passivation same layer	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 13:31
S4	10	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and passivation same layer	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 13:36
S5	6	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and passivation same layer and deposit\$6 and array\$6 and gate same electrode\$1	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 13:40
S6	6	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and passivation same layer and deposit\$6 and array\$6 and gate same electrode\$1 and insulat\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 13:40

S7	4	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and passivation same layer and deposit\$6 and array\$6 and gate same electrode\$1 and insulat \$6 and semiconduct\$6 same channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode \$1 and pad\$1 and contact\$6 same layer \$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 13:43
S8	4	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and passivation same layer and deposit\$6 and array\$6 and gate same electrode\$1 and insulat \$6 and semiconduct\$6 and channel same layer \$6 and source\$6 same electrode\$1 and drain \$6 same electrode\$1 and pad\$1 and contact \$6 same layer\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 13:44
S9	4	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and passivation same layer and deposit\$6 and array\$6 and gate same electrode\$1 and insulat \$6 and semiconduct\$6 and channel same layer \$6 and source\$6 same electrode\$1 and drain \$6 same electrode\$1 and pad\$1 and contact \$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 14:18

S10	7	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and deposit \$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain \$6 same electrode\$1 and pad\$1 and contact \$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 15:09
S11	8	thin same film\$6 same transistor\$1 same backplane and deposit \$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain \$6 same electrode\$1 and pad\$1 and contact \$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 15:10
S12	10	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and passivation	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:24
S13	4	thin same film\$6 same transistor\$1 same backplane and passivat \$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain \$6 same electrode\$1 and pad\$1 and contact \$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:25

S14	4	thin same film\$6 same transistor\$1 same backplane and passivat\$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:26
S15	17	(thin same film\$6 same transistor\$1 or TFT) and backplane and passivat\$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:26
S16	17	(thin same film\$6 same transistor\$1 or TFT) and backplane and passivat\$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel\$5 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:31
S17	8	thin same film\$6 same transistor\$1 same backplane and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:41

S18	7	thin same film\$6 same transistor\$1 same backplane and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6 and polyimide	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:42
S19	105978	thin same film\$6 same transistor\$1 same backplane and deposit\$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6 adn passivat\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:43
S20	4	thin same film\$6 same transistor\$1 same backplane and deposit\$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6 and passivat\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:44
S21	4	thin same film\$6 same transistor\$1 same backplane and deposit\$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6 and passiv\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:49

S22	30	thin same film\$6 same transistor\$1 and backplane and deposit \$6 and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain \$6 same electrode\$1 and pad\$1 and contact \$6 and passiv\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:50
S23	31	thin same film\$6 same transistor\$1 and backplane and array\$6 and gate same electrode\$1 and insulat \$6 and semiconduct\$6 and channel same layer \$6 and source\$6 same electrode\$1 and drain \$6 same electrode\$1 and pad\$1 and contact \$6 and passiv\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:51
S24	16	thin same film\$6 same transistor\$1 and backplane and array\$6 and gate same electrode\$1 and insulat \$6 and semiconduct\$6 and channel same layer \$6 and source\$6 same electrode\$1 and drain \$6 same electrode\$1 and pad\$1 and contact \$6 and passiv\$6 same layer\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/06 19:58
S25	1056957	input same device and tact\$6 and joystick force sens\$6 same resist\$6 and X same Y same plane\$6 and flex \$6 and plung\$6 same coupl\$6 and dome\$6	USPAT	OR	OFF	2008/03/07 06:43
S26	4	input same device and tact\$6 and joystick and force\$6 and sens\$6 same resist\$6 and X same Y same plane\$6 and flex\$6 and plung \$6 same coupl\$6 and dome\$6	USPAT	OR	OFF	2008/03/07 06:44

S27	4	input same device and tact\$6 and joystick and force\$6 and sens\$6 same resist\$6 and X same Y same plane\$6 and flex\$6 and plung \$6 same coupl\$6 and dome\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/07 06:44
S28	2888	(438/149.ccls. or 257/72.ccls.)	USPAT	OR	OFF	2008/03/09 10:21
S29	2013	(438/149.ccls. or 257/72.ccls.) and TFT	USPAT	OR	OFF	2008/03/09 10:21
S30	2352	(438/149.ccls. or 257/72.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1)	USPAT	OR	OFF	2008/03/09 10:22
S31	21	(438/149.ccls. or 257/72.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane	USPAT	OR	OFF	2008/03/09 10:22
S32	5	(438/149.ccls. or 257/72.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and passive \$6	USPAT	OR	OFF	2008/03/09 10:22
S33	12	(438/149.ccls. or 257/72.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and passive \$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:23
S34	0	(438/149.ccls. or 257/72.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and passive \$6 and polyimide\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:26
S35	9	(438/149.ccls. or 257/72.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and passive \$6 and polyimide\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:26
S36	9	(438/149.ccls. or 257/72.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and (passive \$6 and layer\$6) and polyimide\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:36

S37	2	(438/149.ccls. or 257/72.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and (passive \$6 same layer\$6) and polyimide\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:50
S38	42	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and (passive \$6 same layer\$6) and polyimide\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:52
S39	0	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and (passive \$6 adj layer\$6) and polyimide\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:52
S40	0	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and (passive \$6 adj layer\$6)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:52
S41	37	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and (passive\$6 adj layer\$6)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:53
S42	3	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and (passive\$6 adj layer\$6) and polyimide same substrate\$1	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:54
S43	0	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and (passive\$6 adj layer\$6) and polyimide same substrate\$1 and backplane	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:57



S44	128	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and polyimide same substrate\$1 and backplane	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:58
S45	27	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and polyimide same substrate\$1 and backplane and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 10:59
S46	8	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and polyimide same substrate\$1 and backplane and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6 and passivation	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 11:00
S47	1002	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and (passivation same layer\$6) and polyimide same substrate\$1	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 11:01
S48	13	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and (passivation same layer\$6) and polyimide same substrate\$1 and backplane	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 11:02

S49	35	thin same film\$6 same transistor\$1 and backplane and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 11:26
S50	17	(thin same film\$6 same transistor\$1 or TFT) same (substrate same backplane) and backplane and array\$6 and gate same electrode\$1 and insulat\$6 and semiconduct\$6 and channel same layer\$6 and source\$6 same electrode\$1 and drain\$6 same electrode\$1 and pad\$1 and contact\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 11:33
S51	36	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and (passive\$6 same layer\$6) and polyimide\$6 same substrate\$1	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 11:56
S52	18	("438"/\$.ccls. or "257"/\$.ccls.) and (TFT or thin\$6 same film\$6 same transistor\$1) and backplane and (passivation same layer\$6) and polyimide\$6 same substrate\$1	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 11:57
S53	0	"20030108664"	USPAT	OR	OFF	2008/03/09 12:18
S54	3	"20030108664"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 12:18

S55	0	"20030108664" and contact same pad\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 12:19
S56	0	"20040180476" and contact\$6 same pad\$6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/09 12:21
S57	19	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and "345"/\$. ocls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/10 11:23
S58	1	thin same film\$6 same transistor\$1 same backplane and polyimide same substrate and "345"/\$. ocls. and passivation	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/10 11:25

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